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L Number	Hits	Search Text	DB	Time stamp
-	720	LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55
-	51	lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55
-	60	lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55
-	479	LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:55
-	74	(lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56
-	178	lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:56
-	249	lateral\$4 near7 (metal adj oxide adj semiconductor\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57
-	2322	lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57
-	10	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57
-	5	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57
-	455	lateral\$4 near7 (DMOS or DMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:57
-	8141	lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/18 17:58

-	9373	(LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconductor\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:02
-	152308	(gate\$1 or electrode\$1) and source\$1 and drain\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:35
-	140917	(field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:36
-	1922	((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconductor\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))) and ((gate\$1 or electrode\$1) and source\$1 and drain\$1) and ((field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 17:36

-	15865	(amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:04
-	39181	(amorphous or amorph\$9) near3 (layer\$1 or substrate\$1 or wafer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:05
-	30917	(amorphous or amorph\$9) near3 film\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:11
-	67049	((amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1)) or ((amorphous or amorph\$9) near3 (layer\$1 or substrate\$1 or wafer\$1)) or ((amorphous or amorph\$9) near3 film\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:11
-	204	((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and ((gate\$1 or electrode\$1) and source\$1 and drain\$1) and ((field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5))) and (((amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1)) or ((amorphous or amorph\$9) near3 (layer\$1 or substrate\$1 or wafer\$1)) or ((amorphous or amorph\$9) near3 film\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:12
-	5147	implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:07

-	69	(((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconductor\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and ((gate\$1 or electrode\$1 and source\$1 and drain\$1) and ((field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5))) and (((amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1)) or ((amorphous or amorph\$9) near3 (layer\$1 or substrate\$1 or wafer\$1)) or ((amorphous or amorph\$9) near3 film\$1))) and (implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:25
-	498	(((amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1)) or ((amorphous or amorph\$9) near3 (layer\$1 or substrate\$1 or wafer\$1)) or ((amorphous or amorph\$9) near3 film\$1)) same (implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:47

	30	<p>((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconductor\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and (((amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1)) or ((amorphous or amorph\$9) near3 (layer\$1 or substrate\$1 or wafer\$1)) or ((amorphous or amorph\$9) near3 film\$1)) same (implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)))</p>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:26
	330	<p>((amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1)) or ((amorphous or amorph\$9) near3 (layer\$1 or substrate\$1 or wafer\$1)) or ((amorphous or amorph\$9) near3 film\$1)) with (implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)))</p>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:47

-	22	(((amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1)) or ((amorphous or amorph\$9) near3 (layer\$1 or substrate\$1 or wafer\$1)) or ((amorphous or amorph\$9) near3 film\$1)) with (implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:50
-	23681	(((amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1)) or ((amorphous or amorph\$9) near3 (layer\$1 or substrate\$1 or wafer\$1)) or ((amorphous or amorph\$9) near3 film\$1)) with (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:51
-	244	(implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) same (((amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1)) or ((amorphous or amorph\$9) near3 (layer\$1 or substrate\$1 or wafer\$1)) or ((amorphous or amorph\$9) near3 film\$1)) with (substrate or wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:51

-	16	((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconductor\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and ((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) same (((amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1)) or ((amorphous or amorph\$9) near3 (layer\$1 or substrate\$1 or wafer\$1)) or ((amorphous or amorph\$9) near3 film\$1)) with (substrate or wafer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/15 18:52
-	720	LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:55
-	51	lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:55
-	60	lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:56
-	479	LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:56
-	74	(lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:56
-	178	lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:56
-	250	lateral\$4 near7 (metal adj oxide adj semiconductor\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:57

-	2322	lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:57
-	10	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:57
-	5	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:57
-	455	lateral\$4 near7 (DMOS or DMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:58
-	8142	lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 17:59
-	9374	(LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:03
-	43547	(amorphous or amorph\$9) same (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:44

-	334	((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconductor\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and ((amorphous or amorph\$9) same (substrate or wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:06
-	5148	implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:13
-	43678	(silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:09
-	25985	implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:22
-	7645	implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:24
-	26134	(implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:25

-	176	((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and (((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and ((amorphous or amorph\$9) same (substrate or wafer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:25
-	152356	(gate\$1 or electrode\$1) and source\$1 and drain\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:36
-	141012	(field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:37

-	120	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and (((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and ((amorphous or amorph\$9) same (substrate or wafer)))) and ((field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:38
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-	109	<p>((gate\$1 or electrode\$1) and source\$1 and drain\$1) and (((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and (((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and ((amorphous or amorph\$9) same (substrate or wafer)))) and ((field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)))</p>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:38
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-	1255	((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconductor\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:44
-	280	((((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconductor\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and (amorphous or amorph\$9)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:45

-	172	((gate\$1 or electrode\$1) and source\$1 and drain\$1) and ((field adj (oxide\$1 or isolat\$5)) or LOCOS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)) and (((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and (amorphous or amorph\$9))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 18:46
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-	280	<p>((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and (((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and ((amorphous or amorph\$9) same (substrate or wafer)))) or (((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and (((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and (amorphous or amorph\$9))</p>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 19:54
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-	848	((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) with (amorphous or amorph\$9) with (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 19:57
-	45	((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) with (amorphous or amorph\$9) with (substrate or wafer)) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconductor\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 19:57
-	1853	((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) same (amorphous or amorph\$9) same (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 19:58

-	78	((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) same (amorphous or amorph\$9) same (substrate or wafer)) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 19:58
-	43237	(crystall\$9 or re-crystall\$9 or (re adj crystall\$9)) with amorph\$9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 21:53
-	8629	gaussian with (distribut\$6 or profil\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 21:55

-	3	<p>(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) with (amorphous or amorph\$9) with (substrate or wafer)) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and ((crystall\$9 or re-crystall\$9 or (re adj crystall\$9)) with amorph\$9) and (gaussian with (distribut\$6 or profil\$4))</p>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 21:56
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-	3	<p>(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) same (amorphous or amorph\$9) same (substrate or wafer)) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconductor\$4) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and ((crystall\$9 or re-crystall\$9 or (re adj crystall\$9)) with amorph\$9) and (gaussian with (distribut\$6 or profil\$4))</p>	<p>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</p>	<p>2002/03/18 21:56</p>
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	6	<p>(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and (((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and ((amorphous or amorph\$9) same (substrate or wafer)))) or (((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) and (((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and (amorphous or amorph\$9))) and ((crystal\$9 or re-crystal\$9 or (re adj crystal\$9)) with amorph\$9) and (gaussian with (distribut\$6 or profil\$4)))</p>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 21:58
Search History	10/20/02 11:11 AM	Page 20		

-	25	<p>(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) with (amorphous or amorph\$9) with (substrate or wafer)) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconduct\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconduct\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconduct\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and ((crystall\$9 or re-crystall\$9 or (re adj crystall\$9)) with amorph\$9)</p>	<p>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</p>	<p>2002/03/18 21:59</p>
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-	35	(((implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 near8 (silicon or Si or "Si" or Ge or "Ge" or germanium)) or (implant\$8 with ((silicon or Si or "Si" or Ge or "Ge" or germanium) near2 (ion\$1 or atom\$1)))) same (amorphous or amorph\$9) same (substrate or wafer)) and ((LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1)) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconductor\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)) or (lateral\$4 near7 (DMOS or DMOSFET\$1)) or (lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)))) and ((crystall\$9 or re-crystall\$9 or (re adj crystall\$9) with amorph\$9)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/18 21:59
-	1	("5874768").PN.	USPAT; US-PGPUB	2002/03/19 16:21

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	876	LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:20			0
2	BRS	L2	93	lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:32			0
3	BRS	L3	79	lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1 or NMOS or PMOS or NMOSFET\$1 or PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:22			0
4	BRS	L4	277	((lateral\$4 adj double adj diffus\$5 adj ((metal adj oxide adj semiconductor\$4) or MOS\$2 or MOSFET\$1 or PMOS\$2 or PMOSFET\$1 or NMOS\$2 or NMOSFET\$1)) or (lateral\$4 adj double-diffus\$5 adj ((metal adj oxide adj semiconductor\$4) or MOS\$2 or MOSFET\$1 or PMOS\$2 or PMOSFET\$1 or NMOS\$2 or NMOSFET\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:27			0
5	BRS	L7	104	lateral\$4 adj diffus\$5 adj3 metal adj oxide adj semiconductor\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:32			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
6	BRS	L5	9	LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:33			0
7	BRS	L6	5	LDNMOS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:35			0
8	BRS	L8	982	1 or 2 or 3 or 4 or 5 or 6 or 7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:35			0
9	BRS	L9	160596	(gate\$1 or electrode\$1) and source\$1 and drain\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:38			0
10	BRS	L10	16999	(amorphous or amorph\$9) near\$1 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:41			0
11	BRS	L11	41155	(amorphous or amorph\$9) near\$1 (layer\$1 or substrate\$1 or wafer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:41			0
12	BRS	L12	10445	(amorphous or amorph\$9) near\$1 surface\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:41			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
13	BRS	L13	5506	implant\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:25			0
14	BRS	L14	9	8 and 9 and (10 or 11 or 12) and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 13:44			0
15	BRS	L15	32605	implant\$8 near15 (silicon or Si or "Si" or Ge or "Ge" or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:44			0
16	BRS	L16	54828	10 or 11 or 12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:26			0
17	BRS	L17	2443	15 same 16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:26			0
18	BRS	L18	9	8 and 17	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:35			0
19	BRS	L19	114	8 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:35			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
20	BRS	L20	2855	(implant\$8 near15 (silicon or Si or "Si" or Ge or "Ge" or germanium)) with (amorphous or amorph\$9)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:44			0
21	BRS	L21	3000	implant\$8 with (silicon or Si or "Si" or Ge or "Ge" or germanium) with (amorphous or amorph\$9)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:50			0
22	BRS	L22	8	8 and 21	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:46			0
23	BRS	L23	3809	(implant\$8 with (silicon or Si or "Si" or Ge or "Ge" or germanium)) same (amorphous or amorph\$9)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:51			0
24	BRS	L24	10	8 and 23	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:51			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
25	BRS	L25	9546	(LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (LDDMOS\$2 or LDD-MOS\$2 or (LDD adj MOS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1) or ((lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4)) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconductor\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDPMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:56			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
26	BRS	L26	9546	(LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1)) or (lateral\$4 oxide adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double adj diffus\$5 adj (MOS\$3 or MOSFET\$1)) or (lateral\$4 near7 (metal adj oxide adj semiconductor\$4)) or (lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1)) or (LDMOS\$2 or LD-PMOS\$2 or (LD adj PMOS\$3) or LDMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1)) or (LDNMOS\$2 or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:58			0
27	BRS	L27	9546	25 or 26	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:59			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
28	BRS	L28	9546	8 or 27	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 14:59			0
29	BRS	L29	123	21 and 28	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 15:01			0
30	BRS	L30	149	23 and 28	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/20 15:01			0

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				((("6303508") or ("6271551") or ("6005284") or ("5969407") or ("5726477") or ("5648288") or ("5376560") or ("5372952") or ("5064773") or ("4933295") or ("5459089") or ("5399883") or ("5318915") or ("20010025987") or ("6333244") or ("6319798") or ("6255154") or ("6207518") or ("6146934") or ("6072216") or ("6054386") or ("6008099") or ("5986311") or ("5970353") or ("5874768") or ("5825066") or ("5795808") or ("5338945") or ("5322802") or ("5270227") or ("4835112") or ("6323518") or ("6268640") or ("6225151") or ("5258633") or ("5086332") or ("6429077") or ("6426258")).PN.					
31	IS&R	L31	38		USPAT; US-PGPUB	2002/10/20 15:41			0
32	BRS	L32	27	23 and 31	USPAT; US-PGPUB	2002/10/20 15:44			0
33	BRS	L33	27	32 and 28	USPAT; US-PGPUB	2002/10/20 15:45			0